23 September 2004

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Hits Search Text DB 6214193.pn. 6099702.pn. USPAT; 2003/04/25 US-PGPUB; 11:32 EPO; JPO; DERWENT 2 3950184.pn. USPAT; 2003/04/25 US-PGPUB; 11:58 EPO; JPO; DERWENT 14 3950184.URPN. USPAT 2003/04/25 11:58 5 ("3141793" | "3656173" | "3950184" | "4451507" | USPAT 2003/04/25 "5084483").PN. 12:01 17 ("3798056" | "3950184" | "4339319" | "4373988" | USPAT 2003/04/25 "4466864" | "4856456" | "5000827" | "5169408" | 13:58 "5312487" | "5340437" | "5472592" | "5670034" | "5677000" | "5893966" | "5930549" | "6077412" | "6099702").PN. 33 5000827.URPN. **USPAT** 2003/04/25 12:04 5169408.URPN. 53 USPAT 2003/04/25 12:41 33 5000827.URPN. USPAT 2003/04/25 12:50 2247 204/212,225,237,275.1.ccls. USPAT; 2003/04/25 US-PGPUB; 13:58 EPO; JPO; DERWENT 773 204/224r.ccls. USPAT; 2003/04/25 US-PGPUB; 13:58 EPO; JPO; DERWENT 204/212,225,237,275.1.ccls. 204/224r.ccls. 2837 USPAT; 2003/04/25 US-PGPUB; 14:00 EPO; JPO; **DERWENT** 2190 118/416,500,501.ccls. USPAT; 2003/04/25 US-PGPUB; 14:01 EPO; JPO; **DERWENT** 5015 (204/212,225,237,275.1.ccls. 204/224r.ccls.) USPAT; 2003/04/25 118/416,500,501.ccls. US-PGPUB: 14:01 EPO; JPO; **DERWENT** 1027 ((204/212,225,237,275.1.ccls. 204/224r.ccls.) USPAT; 2003/04/25 118/416,500,501.ccls.) and (semiconductor or wafer) US-PGPUB; 14:02 EPO; JPO; DERWENT 557 (((204/212,225,237,275.1.ccls. 204/224r.ccls.) USPAT; 2003/04/25 118/416,500,501.ccls.) and (semiconductor or wafer)) US-PGPUB; 14:02 and (spinning or spin or spun or rotate or rotated or EPO; JPO; rotating) DERWENT

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		rotating)) and (recycle or recycling or recylcer or	DERWENT	
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_	3	("5922138"   "6168691"   "6187152").PN.	USPAT	2003/04/25
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j -	0	6352623.URPN.	USPAT	2003/04/25
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-	3776	205/122,123,157,220.ccls. 427/98,299,352.ccls.	USPAT;	2003/04/25
			US-PGPUB;	14:34
			EPO; JPO;	
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-	940	(205/122,123,157,220.ccls. 427/98,299,352.ccls.)	USPAT;	2003/04/25
		and (semiconductor or wafer)	US-PGPUB;	14:34
			EPO; JPO;	
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-	504	((205/122,123,157,220.ccls. 427/98,299,352.ccls.)	USPAT;	2003/04/25
		and (semiconductor or wafer)) and (cleaning or clean	US-PGPUB;	14:35
		or cleaned or rinsed or rinse or rinsing or wash or	EPO; JPO;	
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		and (semiconductor or wafer)) and (cleaning or clean	US-PGPUB;	14:36
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		recovering)		
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		or US-3950184-\$ or US-6551487-\$ or	U5-PGPUB;	11:50
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-	1	2000wo-us28210.ap,prai.	USPAT;	2003/06/10
			US-PGPUB;	11:53
			EPO; JPO;	
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-	16	6099702.URPN.	USPAT	2003/06/10 11:51
-	15	("3798056"   "3950184"   "4339319"   "4373988"	USPAT	2003/06/10 11:51
		"4466864"   "4856456"   "5000827"   "5169408"		1000,00,1011.01
		"5312487"   "5340437"   "5472592"   "5670034"		
		"5677000"   "5893966"   "5930549").PN.		
-	0	6214193.URPN.	USPAT	2003/06/10 11:51
-	17	("3798056"   "3950184"   "4339319"   "4373988"	USPAT	2003/06/10 11:51
		"4466864"   "4856456"   "5000827"   "5169408"	05/7/	2003/00/10 11:51
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		"4339319"   "4373988"   "4466864"   "4856456"	US-PGPUB;	2003/06/10 11:51
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_	12	(/44130703#) (44080301#) (45030077#)	1100.17	11:52
_	12	(("6139703") or ("6080291") or ("5932077") or	USPAT;	2003/06/10
		("5447615") or ("5421987") or ("5344491")).PN.	US-PGPUB;	12:29
			EPO; JPO;	
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-	1	836844.apn.	USPAT;	2003/06/10
			US-PGPUB;	12:47
			EPO; JPO;	
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-	2401	204/199,212,232,263,275.1,297.01,297.06,297.07,297	OBSERAT;	2003/06/10
			US-PGPUB;	12:48
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-	780	204/224r.ccls.	USPAT;	2003/06/10
			US-PGPUB;	12:48
İ			EPO; JPO;	
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-	3033	204/199,212,232,263,275.1,297.01,297.06,297.07,297	O8Sarast;	2003/06/10
		204/224r.ccls.	US-PGPUB;	12:48
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-	73	(204/199,212,232,263,275.1,297.01,297.06,297.07,29	7.085Pel3.;	2003/06/10
		204/224r.ccls.) and ((multiple or plural\$3 or second)	US-PGPUB;	12:49
		near (outlet or withdraw\$3 or collect\$4))	EPO; JPO;	
			DERWENT;	
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-	26	(204/199,212,232,263,275.1,297.01,297.06,297.07,29		2003/06/10
		204/224r.ccls.) and ((multiple or plural\$3) near	US-PGPUB;	12:49
		(outlet or withdraw\$3 or collect\$4))	EPO; JPO;	
			DERWENT;	
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-	47	((204/199,212,232,263,275.1,297.01,297.06,297.07,29		2003/06/10
		204/224r.ccls.) and ((multiple or plural\$3 or second)	US-PGPUB;	12:52
		near (outlet or withdraw\$3 or collect\$4))) not	EPO; JPO;	
		((204/199,212,232,263,275.1,297.01,297.06,297.07,29		
		204/224r.ccls.) and ((multiple or plural\$3) near	IBM_TDB	
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-	16	(204/199,212,232,263,275.1,297.01,297.06,297.07,29	7 OPSPAIT:	2003/06/10
		204/224r.ccls.) and (situ near (rins\$3 or process\$3	US-PGPUB;	12:56
	ĺ	or clean\$3 or wash\$3))	EPO; JPO;	12.50
		.,,	DERWENT;	
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_	2	5932077.pn.	USPAT;	2004/01/07
			US-PGPUB;	14:58
			EPO; JPO;	14.30
			DERWENT;	
	·		IBM_TDB	
_	25	5932077.URPN.	USPAT	2004/01/07
			001 A 1	14:58
-	64	204/198,199.ccls. and (microelectronic or wafer or	USPAT;	2004/01/07
		semiconductor)	US-PGPUB;	15:12
			EPO; JPO;	13.12
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_	18	204/198,199.ccls. and (microelectronic or wafer or	IBM_TDB USPAT;	2004/01/07
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_	2342	204/212,225,237,275.1.ccls.	IBM_TDB	2004/04/06
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			US-PGPUB;	09:18
			EPO; JPO;	
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- 2957 204/212,225,237,275.1.ccls. 204/224r.ccls. USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT US-PGPUB; EPO;	08 08
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- 14 ((204/212,225,237,275.1.ccls. 204/224r.ccls.) and (Spray\$5 or nozzle))  DERWENT USPAT; 2004/01/0 US-PGPUB; EPO; JPO;	)8
- 14 ((204/212,225,237,275.1.ccls. 204/224r.ccls.) and USPAT; 2004/01/0 (wafer or semiconductor or microelectronic)) and US-PGPUB; 10:12 (tilt\$5 and (spray\$5 or nozzle))	)8
(wafer or semiconductor or microelectronic)) and US-PGPUB; 10:12 (tilt\$5 and (spray\$5 or nozzle)) EPO; JPO;	,,
(tilt\$5 and (spray\$5 or nozzle)) EPO; JPO;	
- 100 (204/198-227.ccls. and (microelectronic or wafer or USPAT; 2004/01/0	18
semiconductor)) and ((contact or electrode or US-PGPUB; 11:48	<i>7</i> 0
cathode) with (clean\$3 or wash\$3 or rins\$5))  EPO; JPO;	
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semiconductor) US-PGPUB; 09:53	
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semiconductor)) and (tilt\$4 with (wafer or substrate   US-PGPUB;   09:53	
or semiconductor or microelectronic)) EPO; JPO;	
DERWENT	
- 5 6613214.pn. 6258220.pn. USPAT; 2004/01/0	9
US-PGPUB; 09:44	
EPO; JPO;	
DERWENT	
- 3 6251236.pn. 6258220.pn. USPAT; 2004/01/0	9
US-PGPUB; 09:44	
EPO; JPO;	
DERWENT	Į
- 11422 (205/\$.ccls. or 204/\$.ccls.) and (microelectronic or USPAT; 2004/01/0	9
wafer or semiconductor) US-PGPUB; 09:53	i
EPO; JPO;	
DERWENT	1

	121	(1005 14 1 001 14 1 ) 1 ( )	T	T
-	121	((205/\$.ccls. or 204/\$.ccls.) and (microelectronic or	USPAT;	2004/01/09
		wafer or semiconductor)) and (tilt\$4 with (wafer or	US-PGPUB;	09:54
		substrate or semiconductor or microelectronic))	EPO; JPO;	
			DERWENT	
-	101	(((205/\$.ccls. or 204/\$.ccls.) and (microelectronic or	USPAT;	2004/01/09
		wafer or semiconductor)) and (tilt\$4 with (wafer or	U5-PGPUB;	09:54
		substrate or semiconductor or microelectronic))) not	EPO; JPO;	
		((204/198-227.ccls. and (microelectronic or wafer or	DERWENT	
		semiconductor)) and (tilt\$4 with (wafer or substrate		
		or semiconductor or microelectronic)))		
-	1554	422/292,300.ccls.	USPAT;	2004/09/23
			US-PGPUB;	10:54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	16	422/292,300.ccls. and (wafer or microelectronic)	USPAT;	2004/09/23
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	10:54
			EPO; JPO;	10.01
			DERWENT;	
-			IBM_TDB	
_	21646	(clean\$3 or rins\$3) near3 (wafer or microelectronic)	USPAT;	2004/09/23
		(4.5-1.140 of Fine Co) hour of (water of fine focioe field)	US-PGPUB;	10:55
			EPO; JPO;	10.55
			DERWENT;	
			IBM_TDB	
_	21418	(clean\$3 or rins\$3) near3 (wafer or	USPAT;	2004/09/23
		microelectro((clean\$3 or rins\$3) near3 (wafer or	US-PGPUB;	10:55
]		microelectronic)) and (spray or stream)nic)	EPO; JPO;	10.55
		mercencerrence), and (spray or stream), me)	DERWENT;	
] .			IBM_TDB	
_	4282	((clean\$3 or rins\$3) near3 (wafer or	USPAT;	2004/09/23
	1202	microelectronic)) and (spray or stream)	US-PGPUB;	
		microelectrome) and (spray or stream)		10:55
			EPO; JPO; DERWENT;	
_	3472	(((clean\$3 or rins\$3) near3 (wafer or	IBM_TDB	2004/00/22
	J-7.2	microelectronic)) and (spray or stream)) and	USPAT;	2004/09/23
		(chemical or fluid)	US-PGPUB;	10:55
		(chemical of Huld)	EPO; JPO;	
			DERWENT;	
_	2269	((((clean\$3 or rins\$3) near3 (wafer or	IBM_TDB	2004/00/00
	2209	microelectronic)) and (spray or stream)) and	USPAT;	2004/09/23
		(chemical or fluid)) and (chamber or container)	US-PGPUB;	10:56
		(chemical or fluid)) and (chamber or container)	EPO; JPO;	
			DERWENT;	
_	4644	134/\$ cold and (wafen on wisers to street )	IBM_TDB	0004/05/55
-	4044	134/\$.ccls. and (wafer or microelectronic)	USPAT;	2004/09/23
			US-PGPUB;	10:56
			EPO; JPO;	
	ľ	İ	DERWENT;	
			IBM_TDB	

-	452	134/58r,94.1,95.1,95.2,95.3,103.2,198.ccls. and	USPAT;	2004/09/23
		(wafer or microelectronic)	US-PGPUB;	10:56
			EPO; JPO;	
			DERWENT;	
]			IBM_TDB	
-	320	(134/58r,94.1,95.1,95.2,95.3,103.2,198.ccls. and	USPAT;	2004/09/23
		(wafer or microelectronic)) and (clean\$3 or rins\$3)	US-PGPUB;	10:56
ľ		near3 (wafer or microelectronic)	EPO; JPO;	
j			DERWENT;	
			IBW_TDB	
-	196	((134/58r,94.1,95.1,95.2,95.3,103.2,198.ccls. and	USPAT;	2004/09/23
1		(wafer or microelectronic)) and (clean\$3 or rins\$3)	US-PGPUB;	10:57
		near3 (wafer or microelectronic)) and (spray or	EPO; JPO;	
		stream)	DERWENT;	-
	132	////124/55: 0410510520521022100	IBM_TDB	
_	132	(((((134/58r,94.1,95.1,95.2,95.3,103.2,198.ccls. and	USPAT;	2004/09/23
		(wafer or microelectronic)) and (clean\$3 or rins\$3) near3 (wafer or microelectronic)) and (spray or	US-PGPUB;	10:57
		stream)) and (chemical or fluid)) and (chamber or	EPO; JPO;	
		container)) and (rais\$3 or lower\$3 or vertical\$4)	DERWENT;	
_	2	6050275.pn.	IBM_TDB USPAT:	2004/00/22
ĺ	-	ооош, о.рп.	US-PGPUB:	2004/09/23
			EPO; JPO;	10.57
			DERWENT;	
			IBM_TDB	